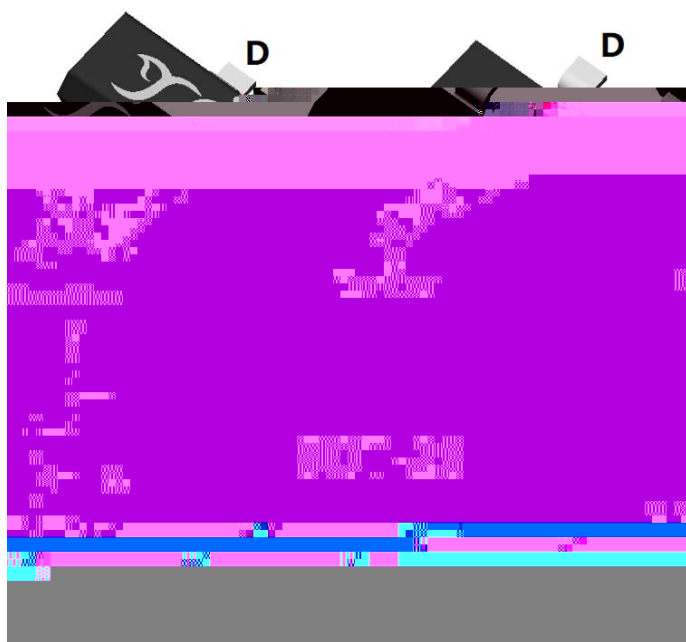




- $R_{DS(ON)}$ (at $V_{GS}=4.5V$)
100mohm
120mohm
- Trench Power MV MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$

			Unit
Drain-source Voltage		V_{DS}	60 V
Gate-source Voltage		V_{GS}	± 20 V
Drain Current	$T_A=25$	I_D	3 A
	$T_A=70$		2.4 A
Pulsed Drain Current ^A		I_{DM}	12 A
Total Power Dissipation	$T_A=25$	P_D	1.2 W
	$T_A=70$		0.8 W
Thermal Resistance Junction-to-Ambient ^B		$R_{\theta JA}$	104 / W
Junction and Storage Temperature Range		T_J, T_{STG}	-55 +150



(Example)

YJL03N06AQ	F2	S10.	3000	30000	120000	7" reel
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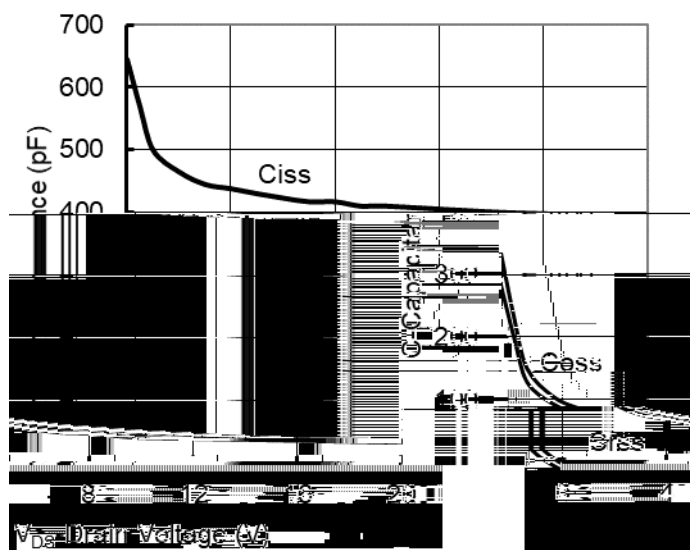
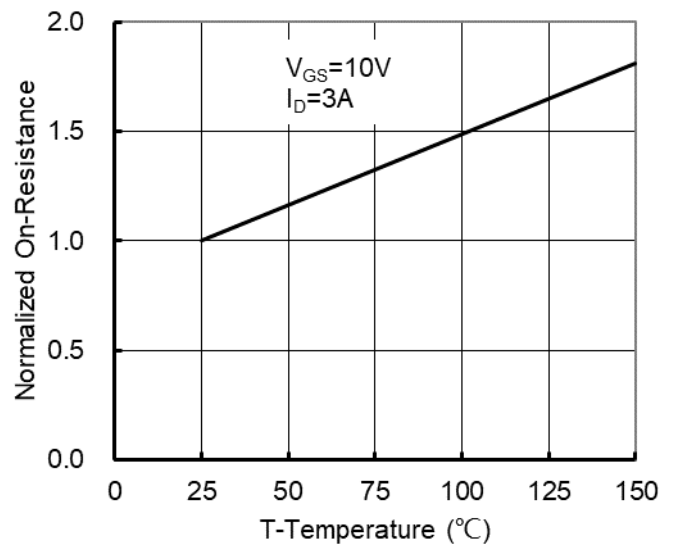
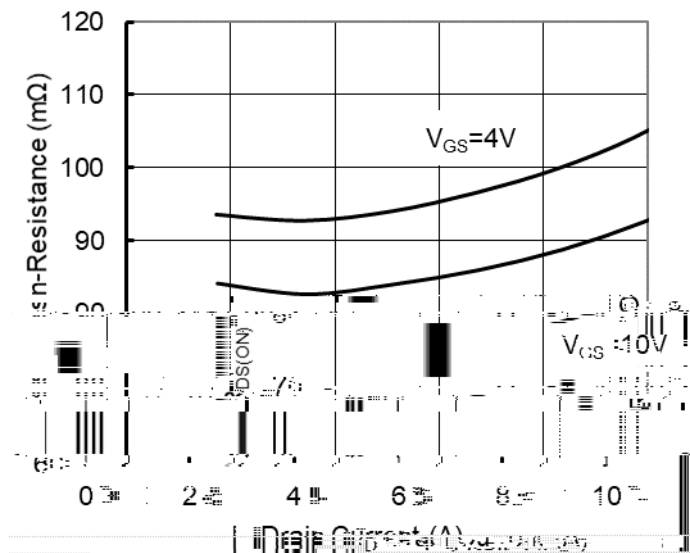
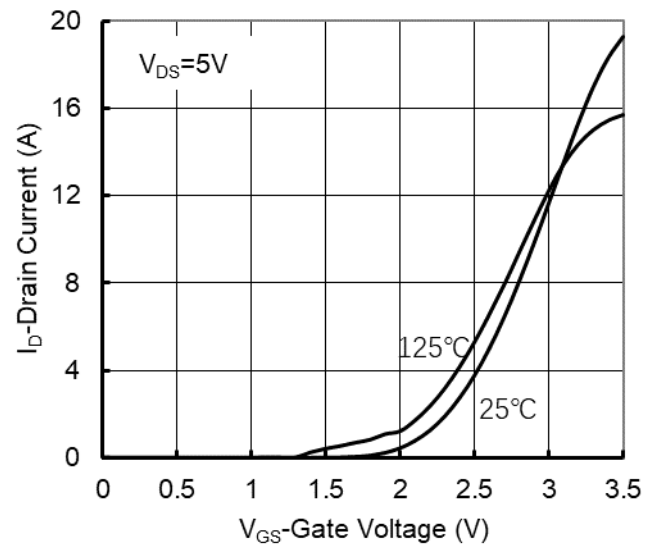
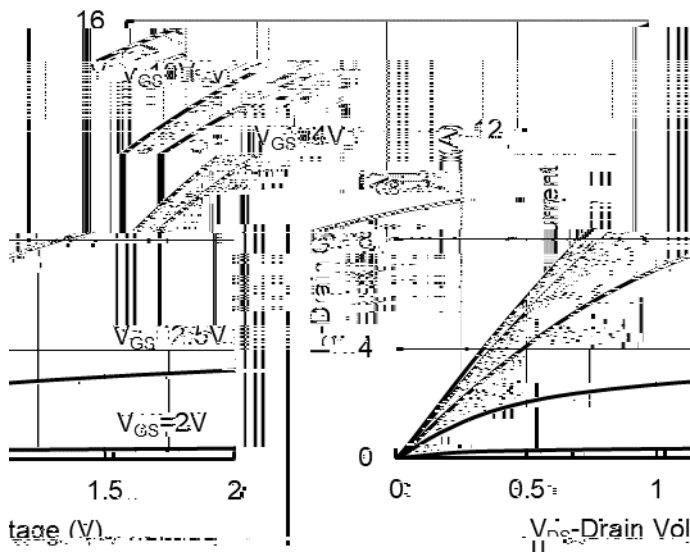
(T_J=25 unless otherwise noted)

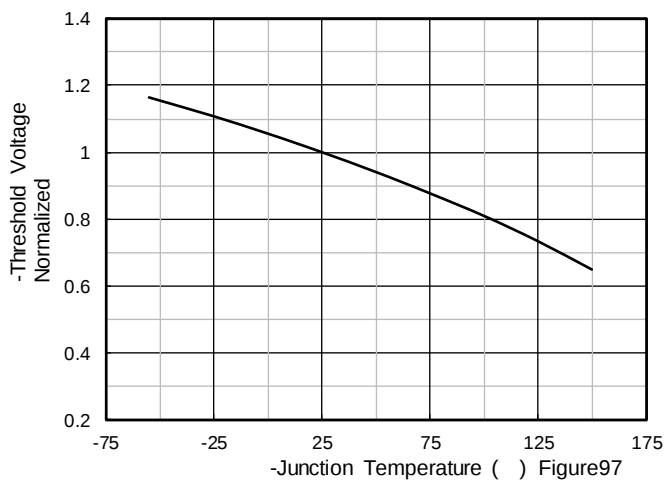
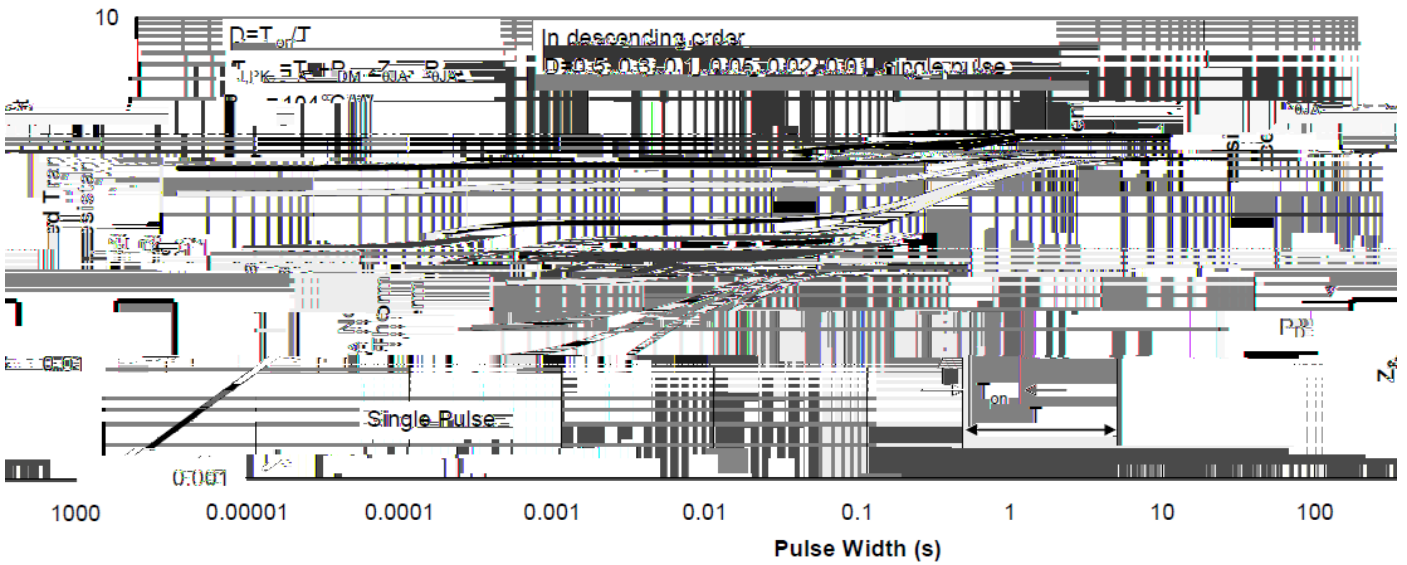
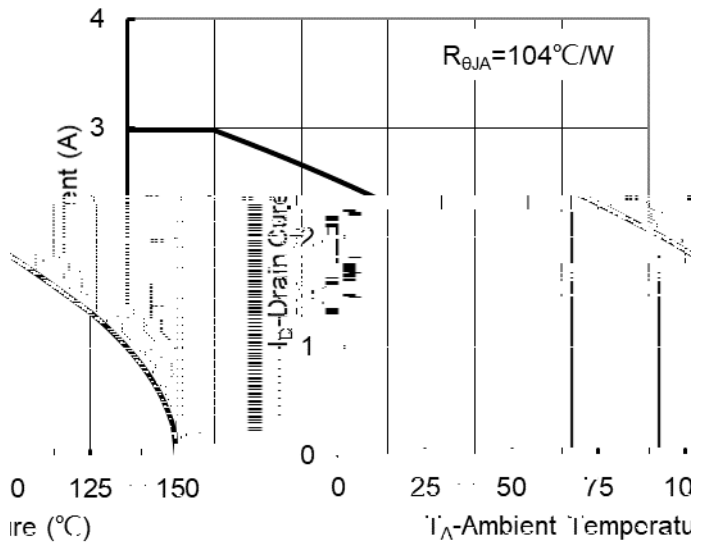
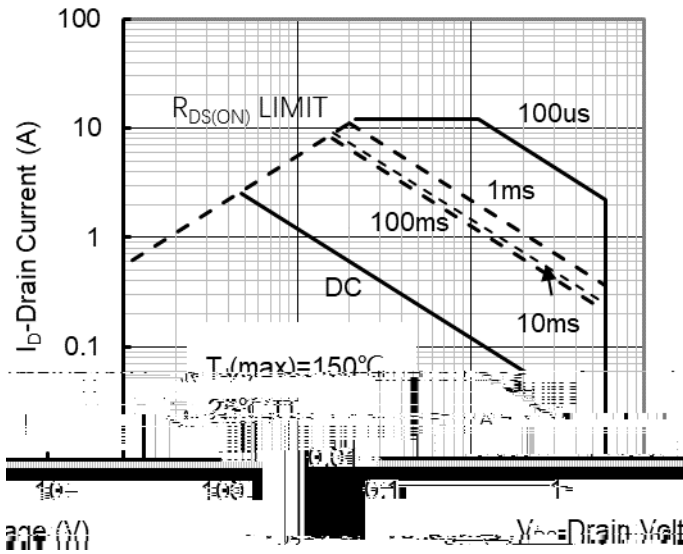
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	60			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V, V _{GS} =0V			1	μA
Gate-Body Leakage Current	I _{GSS1}	V _{GS} =±20V, V _{DS} =0V			±100	nA
	I _{GSS2}	V _{GS} =±10V, V _{DS} =0V			±50	
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D =250μA	0.9	1.3	2.0	V
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =3A		86	100	mΩ
		V _{GS} =4.5V, I _D =2A		92	120	
Diode Forward Voltage	V _{SD}	I _S =3A, V _{GS} =0V			1.2	V
Input Capacitance	C _{iss}	V _{DS} =10V, V _{GS} =0V, f=1MHZ		409		pF
Output Capacitance	C _{oss}			50		
Reverse Transfer Capacitance	C _{rss}			41		

Total Gate Charge

Q_g

V_{GS}=10V, V_{DS}=30V, I_D=3A





\\DQJMLH R